

74LVCH32245A

32-bit bus transceiver with direction pin; 5 V tolerant; 3-state

Rev. 5 — 15 December 2011

Product data sheet

1. General description

The 74LVCH32245A is a 32-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The device features four output enable ($\overline{\text{nOE}}$) inputs for easy cascading and four send/receive (nDIR) inputs for direction control. Pin $\overline{\text{nOE}}$ controls the outputs so that the buses are effectively isolated.

Inputs can be driven from either 3.3 V or 5 V devices. When disabled, up to 5.5 V can be applied to the outputs. These features allow the use of these devices in mixed 3.3 V and 5 V applications.

To ensure the high-impedance state during power-up or power-down, pin $\overline{\text{nOE}}$ should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Bus hold on data inputs eliminates the need for external pull-up resistors to hold unused inputs.

2. Features and benefits

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 2.3 V to 3.6 V
- CMOS low power consumption
- MULTIBYTE flow-through standard pin-out architecture
- Low inductance multiple power and ground pins for minimum noise and ground bounce
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- High-impedance when $V_{\text{CC}} = 0$ V
- All data inputs have bus hold
- Complies with JEDEC standard:
 - ◆ JESD8-7A (1.65 V to 1.95 V)
 - ◆ JESD8-5A (2.3 V to 2.7 V)
 - ◆ JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115B exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C
- Packaged in plastic fine-pitch ball grid array package



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVCH32245AEC	-40 °C to +125 °C	LFPGA96	plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 × 5.5 × 1.05 mm	SOT536-1

4. Functional diagram

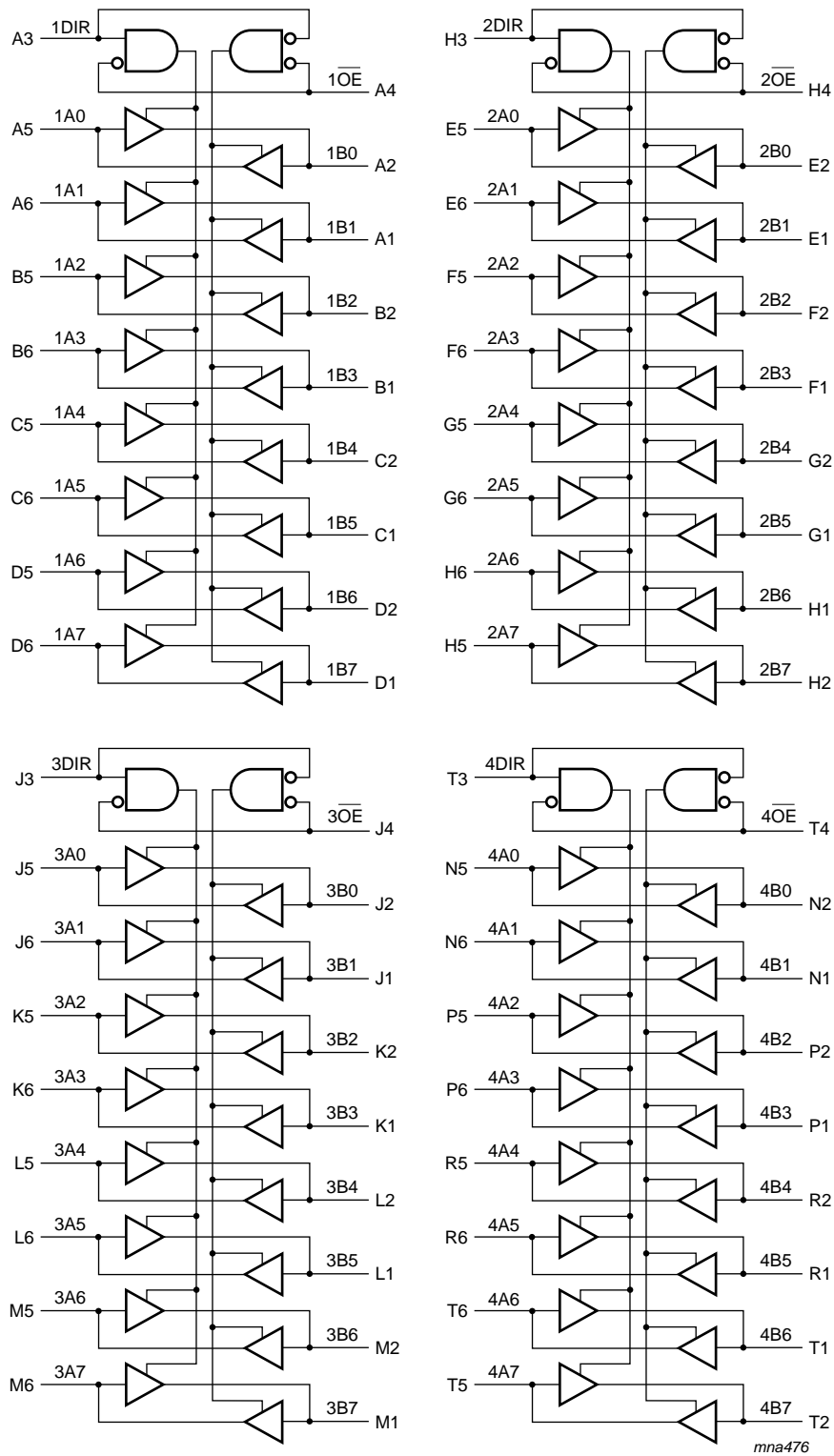


Fig 1. Logic symbol

6. Functional description

Table 3. Function selection

Input		Output		
nOE	nDIR	nAn	nBn	
L	L	A = B	inputs	
L	H	inputs	B = A	
H	X	Z	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		[1] -0.5	+6.5	V
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
V _O	output voltage	output HIGH or LOW state	[2] -0.5	V _{CC} + 0.5	V
		output 3-state	[2] -0.5	+6.5	V
I _O	output current	V _O = 0 V to V _{CC}	-	±50	mA
I _{CC}	supply current		[3] -	200	mA
I _{GND}	ground current		[3] -200	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[4] -	1000	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] All supply and ground pins connected externally to one voltage source.

[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	-	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage	output HIGH or LOW state	0	-	V _{CC}	V
		output 3-state	0	-	5.5	V
T _{amb}	ambient temperature	in free air	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.3 V to 2.7 V	-	-	20	ns/V
		V _{CC} = 2.7 V to 3.6 V	-	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	1.08	-	-	1.08	-	V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	0.65 × V _{CC}	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.12	-	0.12	V
		V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = -100 μA; V _{CC} = 1.65 V to 3.6 V	V _{CC} - 0.2	-	-	V _{CC} - 0.3	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	-	-	1.05	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.8	-	-	1.65	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	-	-	2.05	-	V
		I _O = -18 mA; V _{CC} = 3.0 V	2.4	-	-	2.25	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.2	-	-	2.0	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 100 μA; V _{CC} = 1.65 V to 3.6 V	-	-	0.2	-	0.3	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	0.65	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.6	-	0.8	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	-	0.6	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	-	0.8	V
I _I	input leakage current	V _{CC} = 3.6 V; V _I = 5.5 V or GND ^[2]	-	±0.1	±5	-	±20	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 3.6 V; V _O = 5.5 V or GND; ^[2]	-	0.1	±5	-	±20	μA
I _{OFF}	power-off leakage current	V _{CC} = 0 V; V _I or V _O = 5.5 V	-	0.1	±10	-	±20	μA
I _{CC}	supply current	V _{CC} = 3.6 V; V _I = V _{CC} or GND; I _O = 0 A	-	0.1	40	-	160	μA
ΔI _{CC}	additional supply current	per input pin; V _{CC} = 2.7 V to 3.6 V; V _I = V _{CC} - 0.6 V; I _O = 0 A	-	5	500	-	5000	μA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND to V _{CC}	-	5.0	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
I _{BHL}	bus hold LOW current	V _{CC} = 1.65; V _I = 0.58 V [3][4]	10	-	-	10	-	μA
		V _{CC} = 2.3; V _I = 0.7 V	30	-	-	25	-	μA
		V _{CC} = 3.0; V _I = 0.8 V	75	-	-	60	-	μA
I _{BHH}	bus hold HIGH current	V _{CC} = 1.65; V _I = 1.07 V [3][4]	-10	-	-	-10	-	μA
		V _{CC} = 2.3; V _I = 1.7 V	-30	-	-	-25	-	μA
		V _{CC} = 3.0; V _I = 2.0 V	-75	-	-	-60	-	μA
I _{BHLO}	bus hold LOW overdrive current	V _{CC} = 1.95 V [3][5]	200	-	-	200	-	μA
		V _{CC} = 2.7 V	300	-	-	300	-	μA
		V _{CC} = 3.6 V	500	-	-	500	-	μA
I _{BHHO}	bus hold HIGH overdrive current	V _{CC} = 1.95 V [3][5]	-200	-	-	-200	-	μA
		V _{CC} = 2.7 V	-300	-	-	-300	-	μA
		V _{CC} = 3.6 V	-500	-	-	-500	-	μA

- [1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.
- [2] The bus hold circuit is switched off when V_I > V_{CC} allowing 5.5 V on the input pin.
- [3] Valid for data inputs only. Control inputs do not have a bus hold circuit.
- [4] The specified sustaining current at the data inputs holds the input below the specified V_I level.
- [5] The specified overdrive current at the data input forces the data input to the opposite logic input state.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nAn to nBn; nBn to nAn; see Figure 4 [2]						
		V _{CC} = 1.2 V	-	13.0	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	1.5	5.2	12.2	1.5	13.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	2.8	6.0	1.0	6.7	ns
		V _{CC} = 2.7 V	1.0	2.7	4.7	1.0	6.0	ns
t _{en}	enable time	nOE to nAn, nBn: see Figure 5 [2]						
		V _{CC} = 1.2 V	-	15.0	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	1.5	5.9	15.0	1.5	16.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	3.3	7.9	1.0	8.8	ns
		V _{CC} = 2.7 V	1.5	3.5	6.7	1.5	8.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.7	5.5	1.0	7.0	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{dis}	disable time	nOE to nAn, nBn; see Figure 5						
		V _{CC} = 1.2 V	-	11.0	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	1.5	4.9	13.1	1.5	14.7	ns
		V _{CC} = 2.3 V to 2.7 V	0.5	2.7	7.1	0.5	7.9	ns
		V _{CC} = 2.7 V	1.5	3.4	6.6	1.5	8.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	3.3	5.6	1.5	7.0	ns
t _{sk(o)}	output skew time	V _{CC} = 3.0 V to 3.6 V	-	-	1.0	-	1.5	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC}						
		V _{CC} = 1.65 V to 1.95 V	-	11.5	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	15.2	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	18.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2, 1.8, 2.5 V, 2.7 V, and 3.3 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

t_{en} is the same as t_{PZL} and t_{PZH}.

t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz; f_o = output frequency in MHz

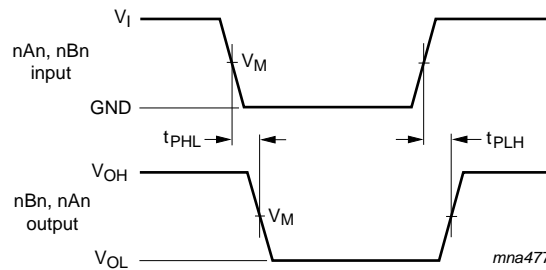
C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

11. Waveforms

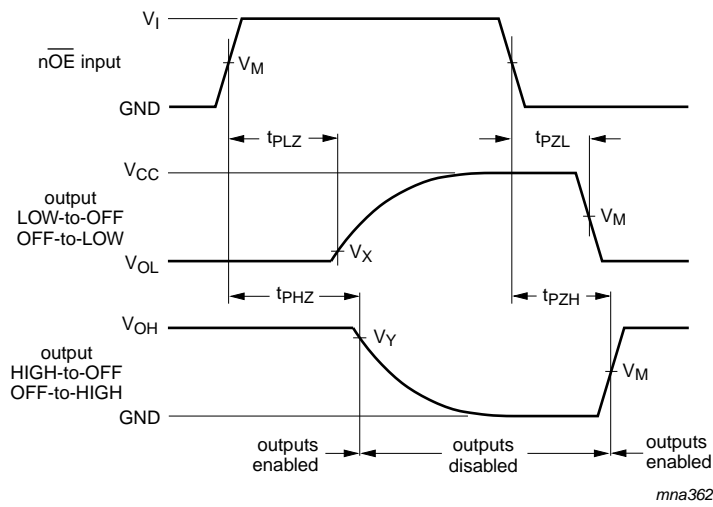


V_M = 1.5 V at V_{CC} ≥ 2.7 V.

V_M = 0.5 × V_{CC} at V_{CC} < 2.7 V.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 4. The input (nAn, nBn) to output (nBn, nAn) propagation delays



$V_M = 1.5 \text{ V}$ at $V_{CC} \geq 2.7 \text{ V}$.

$V_M = 0.5 \times V_{CC}$ at $V_{CC} < 2.7 \text{ V}$.

$V_X = V_{OL} + 0.3 \text{ V}$ at $V_{CC} \geq 2.7 \text{ V}$;

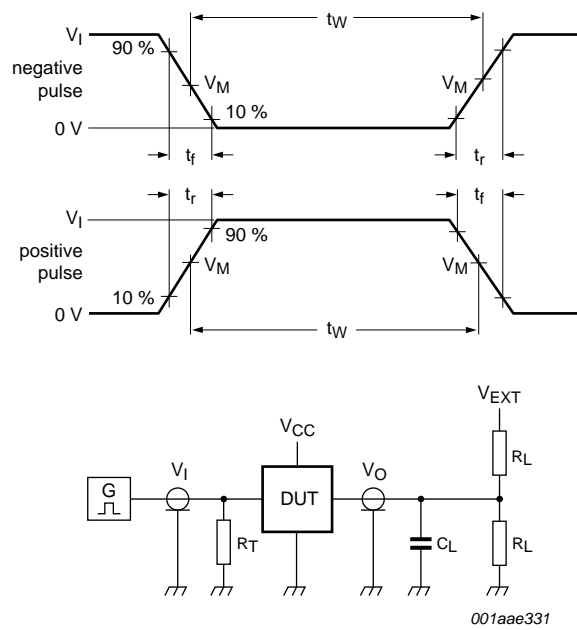
$V_X = V_{OL} + 0.15 \text{ V}$ at $V_{CC} < 2.7 \text{ V}$.

$V_Y = V_{OH} - 0.3 \text{ V}$ at $V_{CC} \geq 2.7 \text{ V}$;

$V_Y = V_{OH} - 0.15 \text{ V}$ at $V_{CC} < 2.7 \text{ V}$.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. 3-state enable and disable times.



Test data is given in [Table 8](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 6. Load circuitry for switching times

Table 8. Test data

Supply voltage	Input		Load		V_{EXT}		
	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PLZ}, t_{PZL}	t_{PHZ}, t_{PZH}
1.2 V	V_{CC}	≤ 2 ns	30 pF	1 k Ω	open	$2 \times V_{CC}$	GND
1.65 V to 1.95 V	V_{CC}	≤ 2 ns	30 pF	1 k Ω	open	$2 \times V_{CC}$	GND
2.3 V to 2.7 V	V_{CC}	≤ 2 ns	30 pF	500 Ω	open	$2 \times V_{CC}$	GND
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$	GND
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$	GND

12. Package outline

LFBGA96: plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 x 5.5 x 1.05 mm SOT536-1

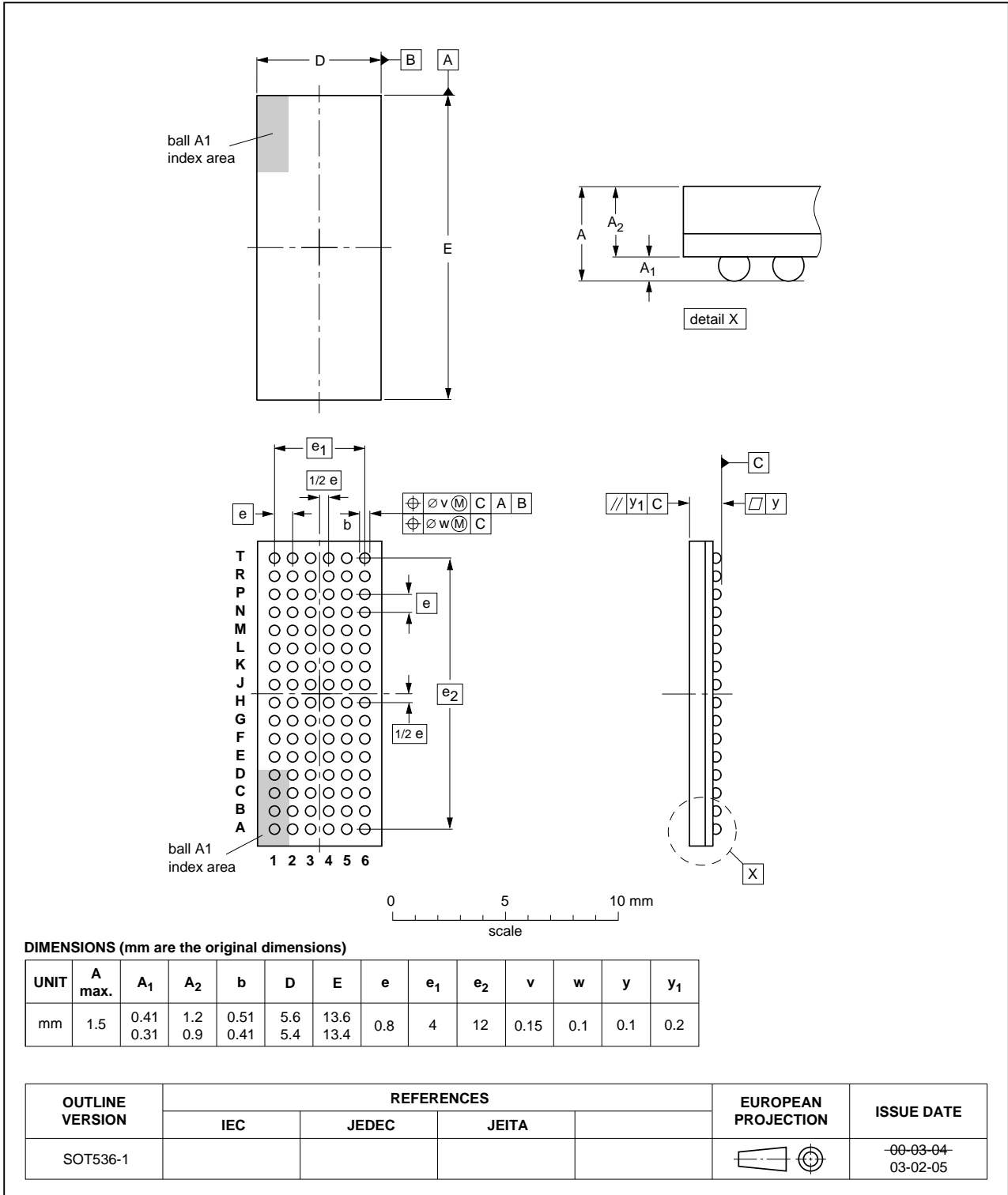


Fig 7. Package outline SOT536-1 (LFBGA96)

13. Abbreviations

Table 9. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVCH32245A v.5	20111215	Product data sheet	-	74LVCH32245A v.4
Modifications:	<ul style="list-style-type: none"> Maximum propagation delay value for $V_{CC} = 1.65\text{ V}$ to 1.95 V at $+125\text{ }^{\circ}\text{C}$ changed from 12.9 ns to 13.8 ns Maximum enable time value for $V_{CC} = 1.65\text{ V}$ to 1.95 V at $+125\text{ }^{\circ}\text{C}$ changed from 15.8 ns to 16.9 ns Maximum disable time value for $V_{CC} = 1.65\text{ V}$ to 1.95 V at $+125\text{ }^{\circ}\text{C}$ changed from 13.7 ns to 14.7 ns 			
74LVCH32245A v.4	20111109	Product data sheet	-	74LVCH32245A v.3
Modifications:	<ul style="list-style-type: none"> Table 4, Table 5, Table 6, Table 7 and Table 8: values added for lower voltage ranges. 			
74LVCH32245A v.3	20070820	Product data sheet	-	74LVCH32245A v.2
74LVCH32245A v.2	20040511	Product specification	-	74LVC_LVCH32245A v.1
74LVC_LVCH32245A v.1	19990901	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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